

Features

- Low forward voltage drop
- High reverse voltage
- Hermetic metal cases with ceramic insulators

Typical Applications

- All purpose high power rectifier diodes
- High power resistance welding equipment
- Non-controllable and half-controllable rectifiers
- Controlled rectifiers

$I_{F(AV)}$	1200A
V_{RRM}	2100~3000 V
I_{FSM}	12 kA
I^2t	720 10³A²S



SYMBOL	CHARACTERISTIC	TEST CONDITIONS		T _i (°C)	VALUE			UNIT
					Min	Type	Max	
$I_{F(AV)}$	Mean forward current	180° half sine wave 50Hz Double side cooled,	T _c =85°C	160			1200	A
V_{RRM}	Repetitive peak reverse voltage	tp=10ms		160	2100		3000	V
I_{RRM}	Repetitive peak current	At V _{RRM}		160			40	mA
I_{FSM}	Surge forward current	10ms half sine wave		160			12	kA
I^2t	I ² t for fusing coordination	V _R =0.6V _{RRM}					720	A ² s*10 ³
V_{FO}	Threshold voltage			160			0.86	V
r _F	Forward slope resistance						0.35	mΩ
V_{FM}	Peak forward voltage	I _{FM} =1500A, F=15kN		160			1.39	V
Q _{rr}	Recovery charge	I _{FM} =2000A, tp=2000μs, di/dt=-20A/μs, V _R =50V		160		2000		μC
R _{th(j-c)}	Thermal resistance Junction to case	At 180° sine double side cooled Clamping force 15.0kN					0.032	°C / W
R _{th(c-h)}	Thermal resistance case to heat sink					0.010		
F _m	Mounting force				10		20	kN
T _{stg}	Stored temperature				-40		160	°C
W _t	Weight					150		g
Outline								

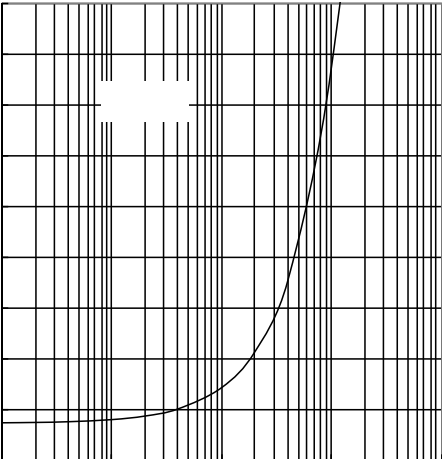


Fig.1

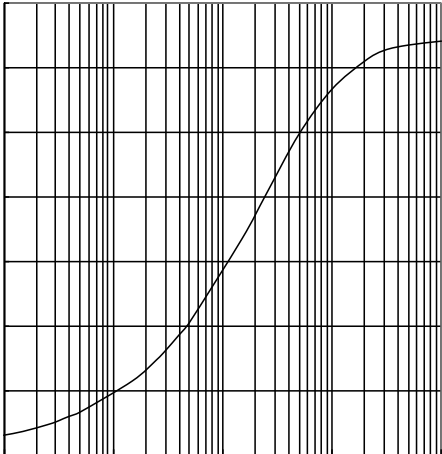


Fig.2

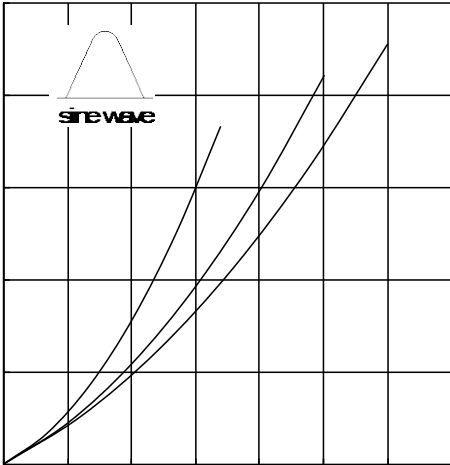


Fig.3

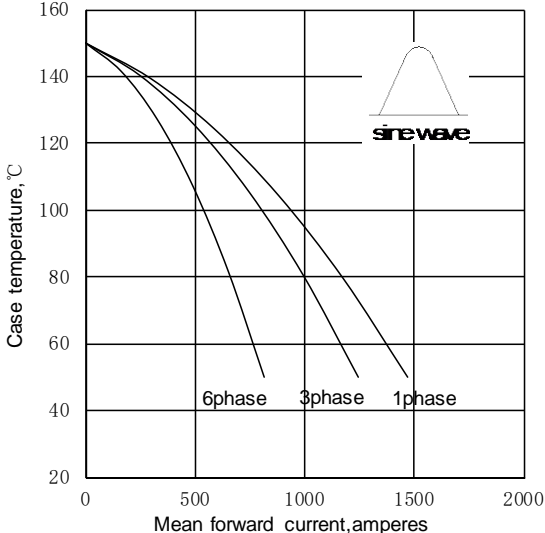


Fig.4

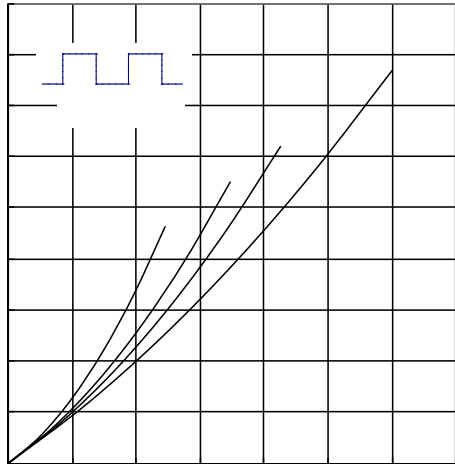


Fig.5

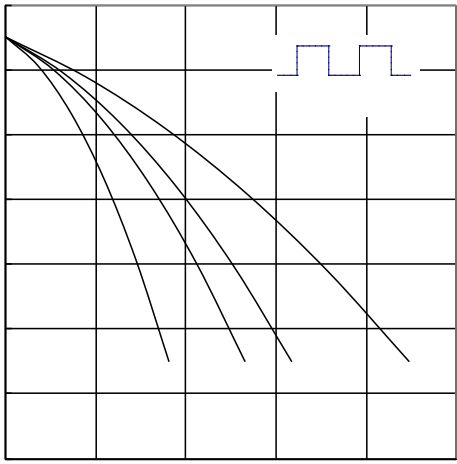


Fig.6

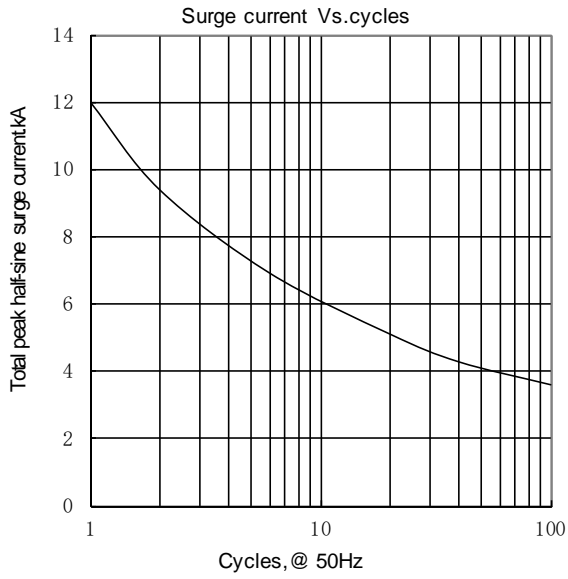


Fig.7

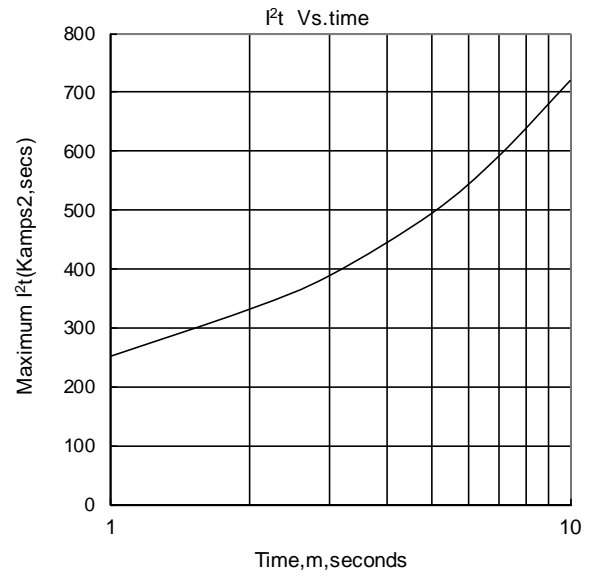


Fig.8

Outline: ZT33aT

